

Docket: 14467.05

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

First Named

Inventor:

John P. Snyder

Appln. No.:

10/796,514

Filing Date:

March 9, 2004

Transistor Having High Dielectric Constant

Title:

Gate Insulating Layer and Source and Drain

Forming Schottky Contact with Substrate

Examiner:

Kim, Su C.

Group Art Unit:

2823

## RESPONSE AND AMENDMENT UNDER 37 C.F.R. 1.111

Mail Stop Amendment Commissioner for Patents P. O. Box 1450 Alexandria, Virginia 22313-1450 I hereby certify that this document is being sent via First Class U. S. mail addressed to: Mail Stop Amendment, Commissioner for Patents, P. O Box 1450, Alexandria, VA 22313-1450, on this 21st day of November, 2005.

Sue Nienaber

Dear Sir:

In response to the Office Action dated May 20, 2005, please amend the above-identified application as follows:

Claims begin on page 2 of this paper.

Remarks begin on page 15 of this paper.